

200V 18A N-Channel Enhancement Mode Power MOSFET

General Description

BXP18N20 is Bridgelux high voltage MOSFET family based on advanced planar DMOS technology. This advanced MOSFET family has optimized on-state resistance, and also provides superior switching performance and higher avalanche energy strength. This device family is suitable for high efficiency switch mode power supplies.

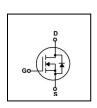
FEATURES

- RDSON≤0.18 Ω @Vgs=10V, Id=9A
- Excellent RDS(ON) and Low Gate Charge

Version: 1.1

- · Fast switching capability
- · Lead free product is acquired

SYMBOL









TO-252

TO-220

TO-220F

ASSEMBLY MESSAGE

Product Name	Package	Packaging
BXP18N20D	TO-252	Tube/Reel
BXP18N20P	TO-220	Tube
BXP18N20F	TO-220F	Tube

ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Parameter		Symbol	Rating			Linit
		Symbol	BXP18N20D	BXP18N20P	BXP18N20F	Unit
Drain-Source Voltage		V _{DSS}	200			V
Drain Current	Continuous (T _C = 25°C)		18			Α
Drain Current	Continuous (T _C = 100°C)	l _D	11			Α
Drain Current Pulsed (Note1)		I _{DM}	72			Α
Gate-Source Voltage		V _{GSS}	±30			V
Avalanche Energy Single Pulse (Note2)		E _{AS}	845			mJ
Avalanche Current (Note1)		I AR	4.2			Α
Peak Diode Recovery dv/dt (Note3)		dv/dt	5			V/ns
Power Dissipation (Note 2)	T _C =25°C	- P _D	90	95	55	W
	Derate above 25°C		0.72	0.76	0.44	W/°C
Maximum Junction Temperature		TJ	150			°C
Storage Temperature Range		T _{STG}	-55 to 150			°C

Note:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L=10mH, I_D =13A, V_{DD} =50V, RG=25 Ω , Starting TJ = 25°C
- 3. $I_{SD} \le 18A$, $di/dt \le 100A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting TJ = 25°C



THERMAL CHARACTERISTICS

Parameter	Symbol		Unit		
Farameter	Symbol	BXP18N20D	BXP18N20P	BXP18N20F	Offic
Thermal Resistance, Junction-to-Case	Rejc	1.38	1.31	2.27	°C/W
Thermal Resistance, Junction-to-Ambient	R _{0JA}	100	62.5	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_J=25°C,unless otherwise Noted)

Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V, ID=250µA	200			V
Zero Gate Voltage Drain Current		VDS=200V, VGS=0V			1	uA
	I _{DSS}	VDS=160V, TC = 125°C			10	uA
Gate-Body Leakage Current, Forward		VGS=30V			100	nA
Gate-Body Leakage Current, Reverse	- I _{GSS}	VGS=-30V			-100	nA
Breakdown Voltage Temperature	△BVDSS/	ID = 250 uA		0.24		VII°C
Coefficient	△TJ	ID = 250 μA		0.24		V/°C
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	VDS=VGS, ID=250µA	2		4	>
Drain-Source On-State Resistance	R _{DS(ON)}	VGS=10V, ID=9A		0.12	0.18	Ω
Forward Transconductance (Note4)	g FS	VDS =15V, ID=18A		18		S
DYNAMIC PARAMETERS						
Input Capacitance	Ciss	VDC-25V VCC-0V		1140		pF
Output Capacitance	Coss	VDS=25V, VGS=0V,		180		pF
Reverse Transfer Capacitance	C _{RSS}	f=1.0MHz		22		pF
SWITCHING PARAMETERS	•		•			
Turn-ON Delay Time	t _{D(ON)}	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\		15		ns
Turn-ON Rise Time	t _R	VDD=100V, ID=18A, VGS =		32		ns
Turn-OFF Delay Time	t _{D(OFF)}	10V ,RG=2.4Ω		28		ns
Turn-OFF Fall-Time	t _F	(Note4,5)		7		ns
Total Gate Charge(Note5)	Q_{G}	VDS =100V, VGS =10V, ID		23		nC
Gate Source Charge	Q _{GS}	=18A		7		nC
Gate Drain Charge	Q_{GD}	(Note4,5)		9		nC
SOURCE- DRAIN DIODE RATINGS	AND CHARA	CTERISTICS		•		
Drain-Source Diode Forward Voltage	V _{SD}	IS=18A, VGS=0V			1.5	V
Diode Continuous Forward Current	Is				18	Α
Pulsed Drain-Source Current	I _{SM}				72	Α
Reverse Recovery Time	t _{RR}	VGS = 0 V, ISD = 18A		165		ns
Reverse Recovery Charge	Q _{RR}	di/dt=100 A/µs (Note4,5)		0.88		uC

Note: 4. Pulse Test : Pulse width $\leq 300\mu$ s, Duty cycle $\leq 2\%$

5. Essentially independent of operating temperature



TYPICAL CHARACTERISTICS

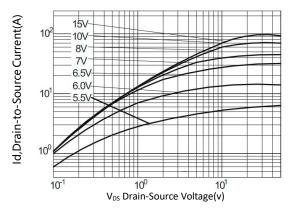


Figure 1. Typical Output Characteristics

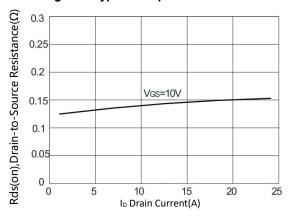


Figure 3. On-Resistance versus Drain Current

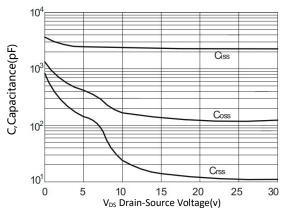


Figure 5. Typical Capacitance versus VDS

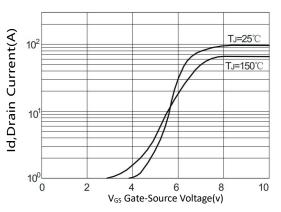


Figure 2. Typical Transfer Characteristics

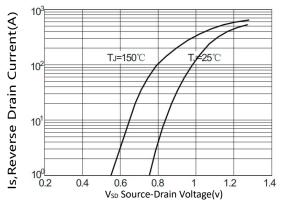


Figure 4. Diode forward voltage versus Current

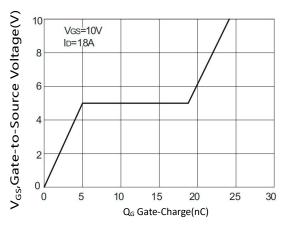


Figure 6. Typical Gate Charge versus V_{GS}



TYPICAL CHARACTERISTICS(Cont.)

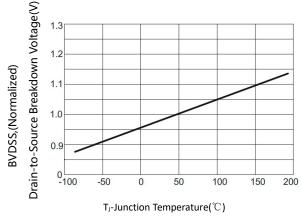


Figure 7. BV_{DSS} Variation with Temperature

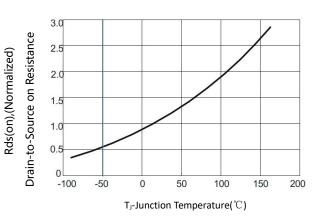


Figure 8. On-Resistance Variation with Temperature

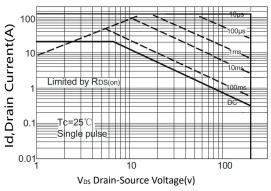


Figure 9. Maximum Safe Operating Area

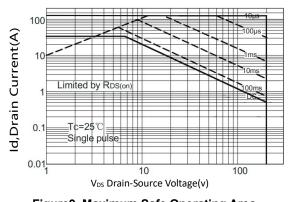


Figure 9. Maximum Safe Operating Area BXP18N20F

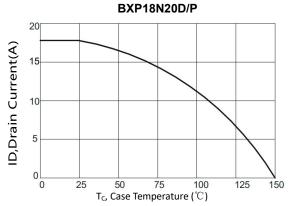
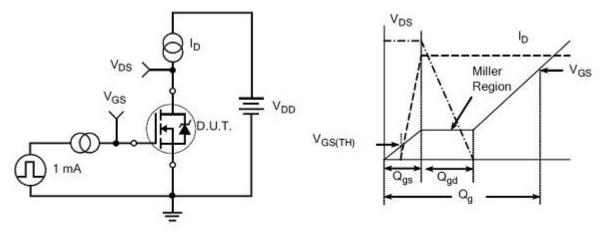


Figure 10. Maximum Continuous Drain Current versus Case Temperature

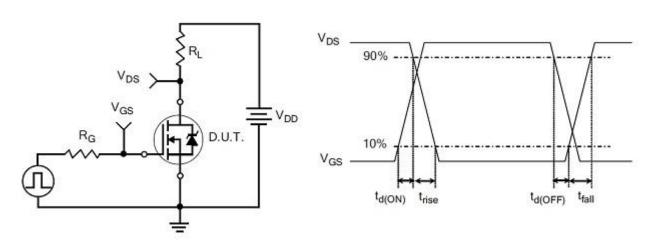


TEST CIRCUITS AND WAVEFORMS



Gate Charge Test Circuit

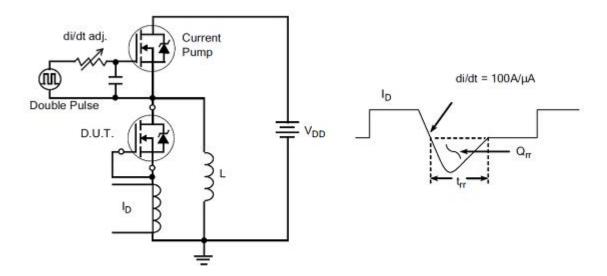
Gate Charge Waveform



Resistive Switching Test Circuit

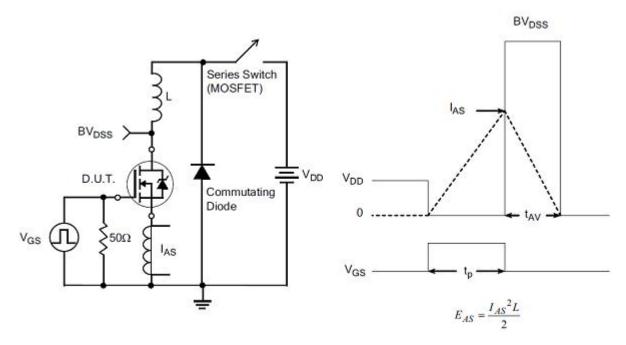
Resistive Switching Waveforms

TEST CIRCUITS AND WAVEFORMS(Cont.)



Diode Reverse Recovery Test Circuit

Diode Reverse Recovery Waveform



Unclamped Inductive Switching Test Circuit

Unclamped Inductive Switching Waveforms





Revision history

Document revision history

Date	Revision	Changes
26-Nov-2021	1.0	First release
6-Jan-2022	1.1	Update parameter



Bridgelux WuXi R&D CO.,LTD

Halogen Free
BXP18N20

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